

HAT2244WP

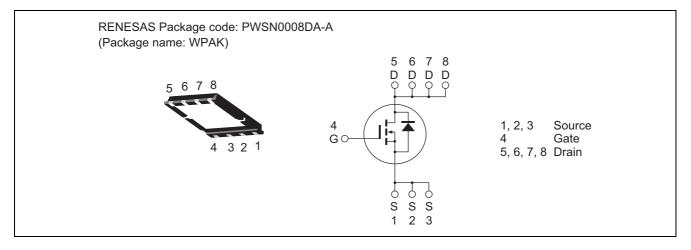
Silicon N Channel Power MOS FET Power Switching

> REJ03G1549-0400 Rev.4.00 Jun 13, 2007

# Features

- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
  - $R_{DS(on)} = 10 \text{ m}\Omega \text{ typ.}$  (at  $V_{GS} = 10 \text{ V}$ )

## Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	80	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	30	А
Drain peak current	Note1 I <sub>D(pulse)</sub>	120	А
Body-drain diode reverse drain current	I <sub>DR</sub>	30	А
Avalanche current	I <sub>AP</sub> Note 2	25	А
Avalanche energy	E <sub>AR</sub> Note 2	83	mJ
Channel dissipation	Pch Note3	25	W
Channel to Case Thermal Impedance	θch-c <sup>Note3</sup>	5	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1.  $PW \leq 10 \ \mu s, \ duty \ cycle \leq 1\%$ 

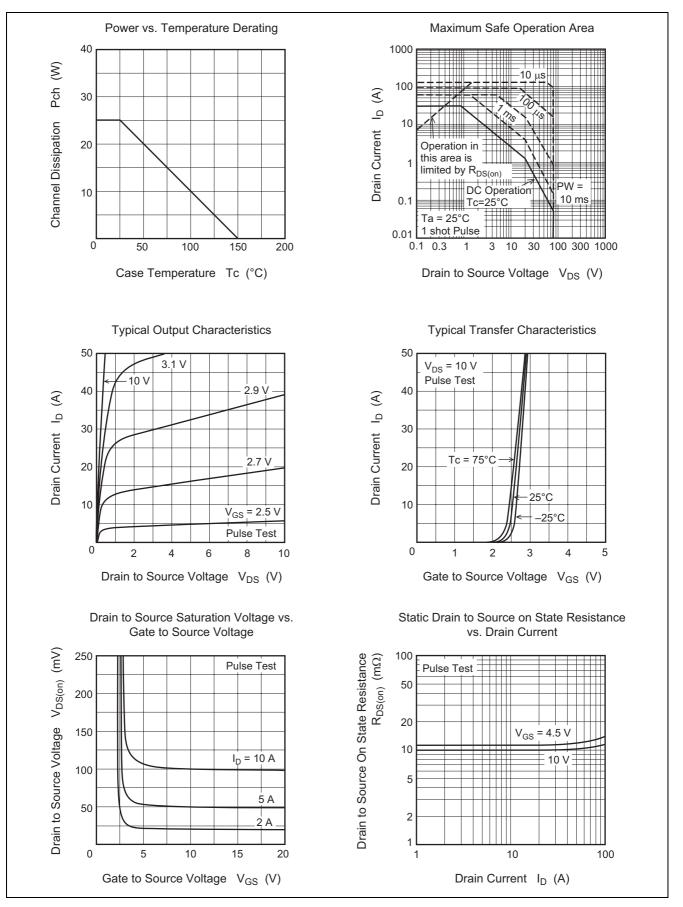
- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3. Tc = 25°C

# **Electrical Characteristics**

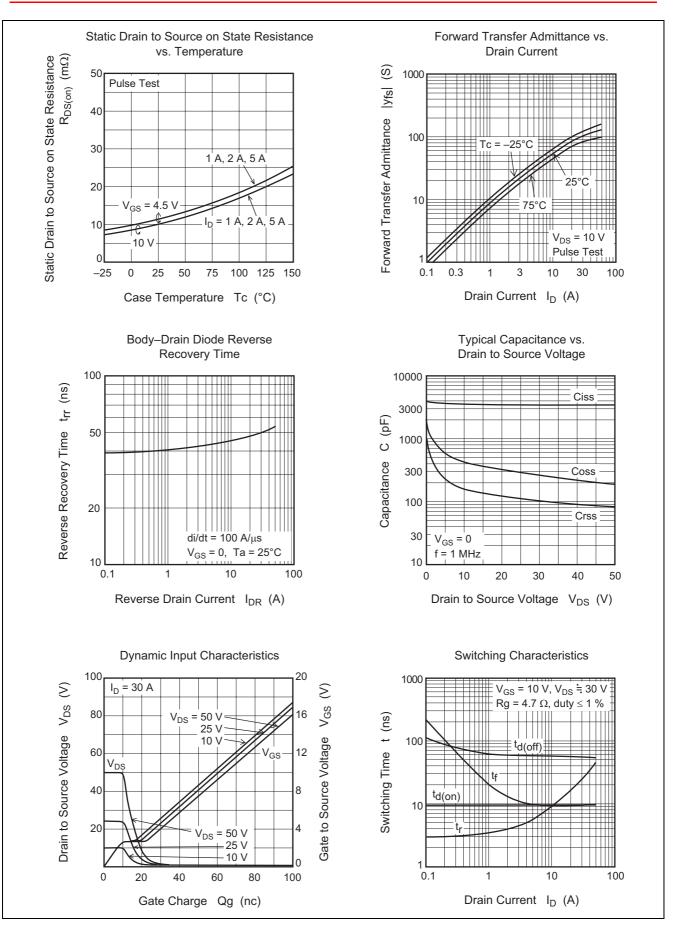
						(Ta = 25°C)
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	80			V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>			± 0.5	μΑ	$V_{GS} = \pm 20 \text{ V}, \text{ V}_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 80 V, V_{GS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	0.8	_	2.3	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	10	12.5	mΩ	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R <sub>DS(on)</sub>	_	11.5	15.5	mΩ	$I_D = 15 \text{ A}, V_{GS} = 4.5 \text{ V}^{Note4}$
Forward transfer admittance	y <sub>fs</sub>	42	70	_	S	$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	3520	_	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss	_	410	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	160	_	pF	f = 1 MHz
Gate Resistance	Rg		1.2		Ω	
Total gate charge	Qg	_	60	_	nC	V <sub>DD</sub> = 25 V
Gate to source charge	Qgs	_	9.5	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	9.0	_	nC	I <sub>D</sub> = 30 A
Turn-on delay time	t <sub>d(on)</sub>	_	9.5	_	ns	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$
Rise time	tr	_	14.5	_	ns	$V_{DD} \cong 30 \text{ V}$
Turn-off delay time	t <sub>d(off)</sub>	_	56		ns	$R_L = 2 \Omega$
Fall time	t <sub>f</sub>	_	9.5	_	ns	Rg = 4.7 Ω
Body-drain diode forward voltage	V <sub>DF</sub>		0.83	1.08	V	$I_F = 30 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>		50		ns	$I_F = 30 \text{ A}, V_{GS} = 0$
						$di_{F}/dt = 100 \text{ A}/\mu \text{s}$

Notes: 4. Pulse test

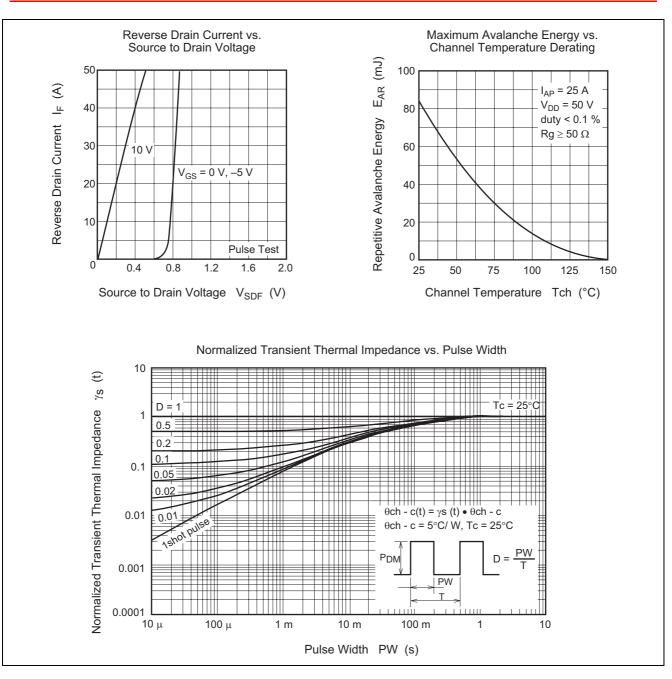
## **Main Characteristics**

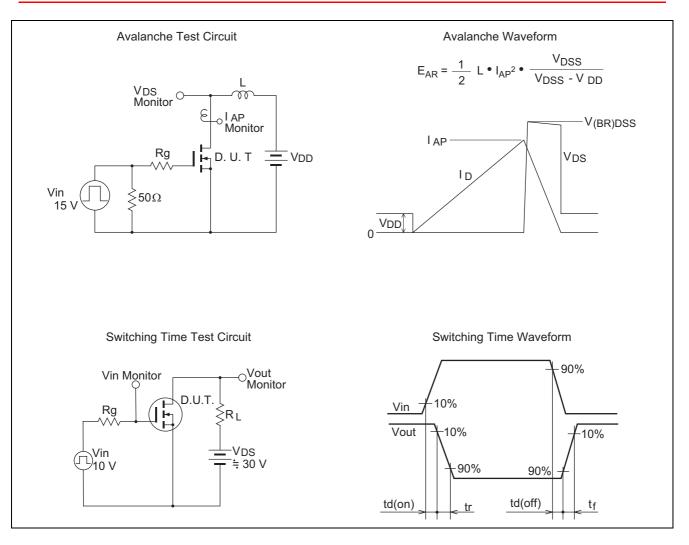


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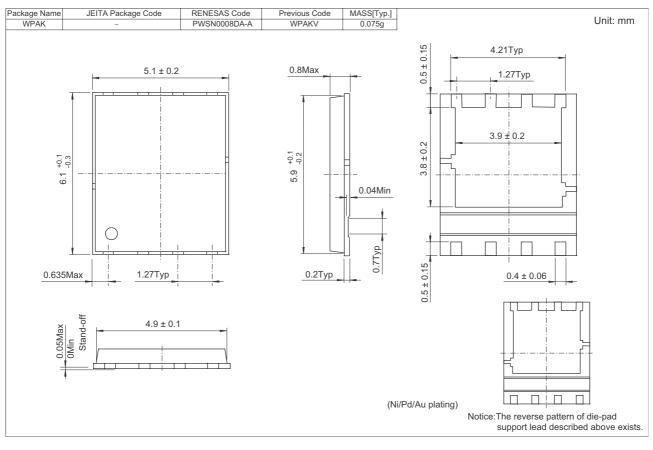


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# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
HAT2244WP-EL-E	2500pcs	Taping

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